**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

# 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	3.7	А
Static characte	Static characteristics						,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	54	72	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



30 V, N-channel Trench MOSFET

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV90ENE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV90ENE	%GH

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{amb}$ = 25 °C; $t \le 5$ s	[1]	-	3.7	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	3	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	1.9	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	12	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	460	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	1.1	W
		T <sub>sp</sub> = 25 °C		-	4.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]		1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

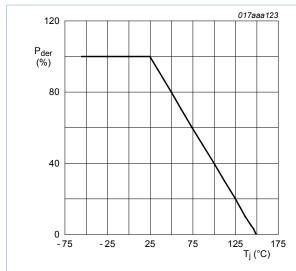


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

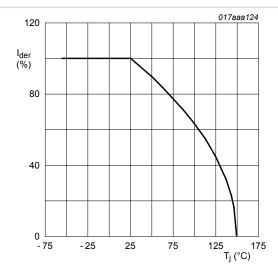


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

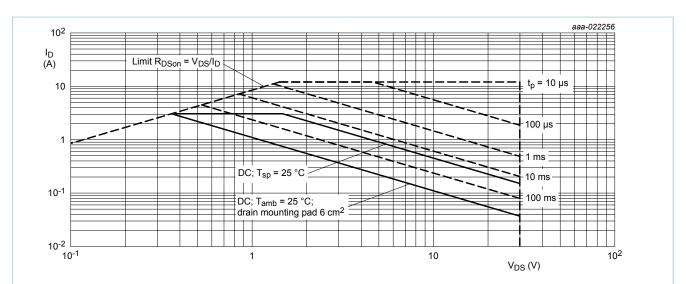


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

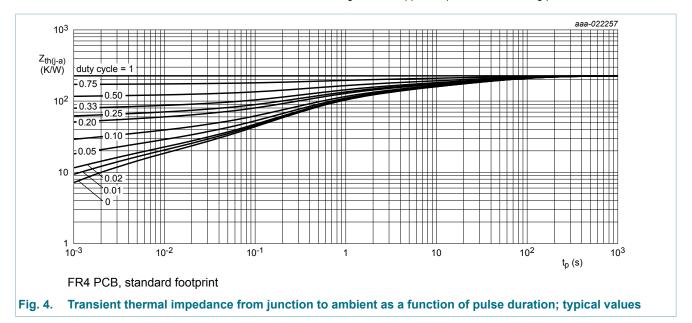
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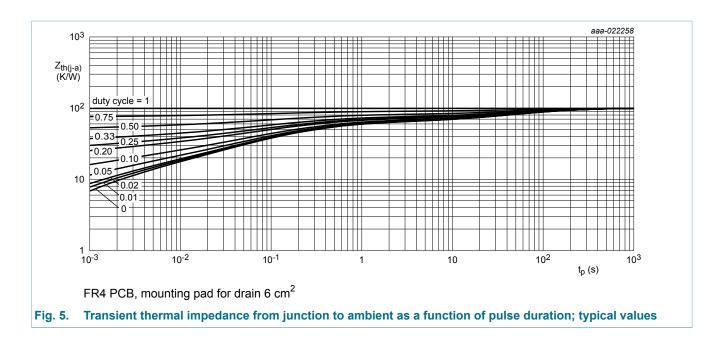
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	227	270	K/W
		<u>[2]</u>	-	99	115	K/W	
	ambient	t ≤ 5 s	<u>[2]</u>	-	66	78	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	20	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.





30 V, N-channel Trench MOSFET

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1	1.5	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub> gate leakage c	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μΑ
R <sub>DSon</sub>		$V_{GS}$ = 10 V; $I_D$ = 3 A; $T_j$ = 25 °C	-	54	72	mΩ
resistance	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 150 °C	-	88	118	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2.6 A; T <sub>j</sub> = 25 °C	-	70	100	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_D$ = 3 A; $T_j$ = 25 °C	-	9	-	S
$R_G$	gate resistance	f = 1 MHz	-	11.5	-	Ω
Dynamic cl	haracteristics	1	1			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 3 A; $V_{GS}$ = 10 V;	-	3.6	5.5	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.4	-	nC
$Q_{GD}$	gate-drain charge		-	0.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	160	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	33	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	26	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $I_{D}$ = 3 A; $V_{GS}$ = 10 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	11	-	ns
t <sub>f</sub>	fall time		-	4	-	ns
Source-dra	in diode				1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

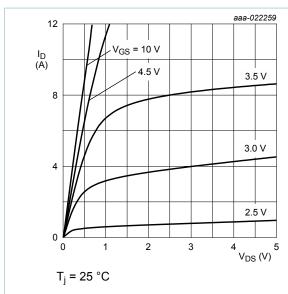


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

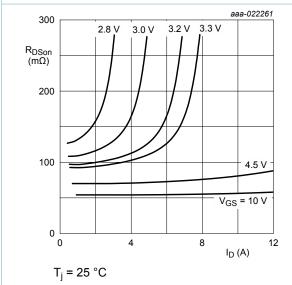


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

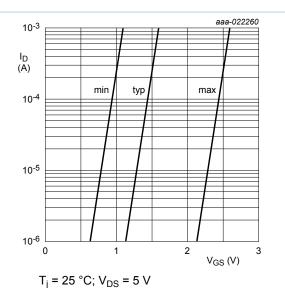


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

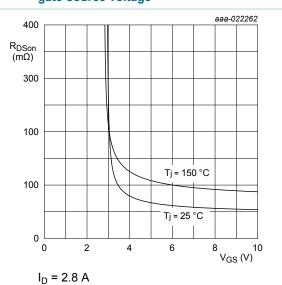


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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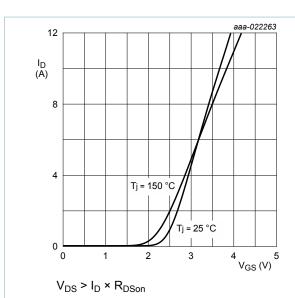


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

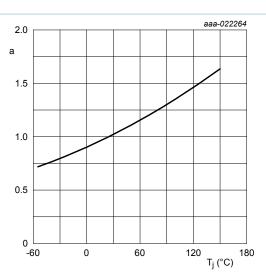


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

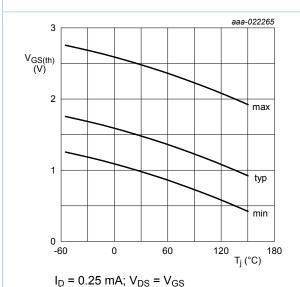


Fig. 12. Gate-source threshold voltage as a function of junction temperature

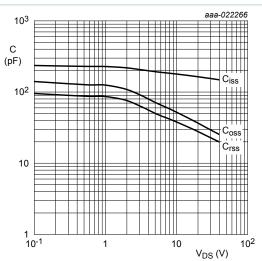


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$ 

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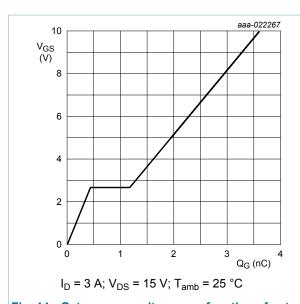


Fig. 14. Gate-source voltage as a function of gate charge; typical values

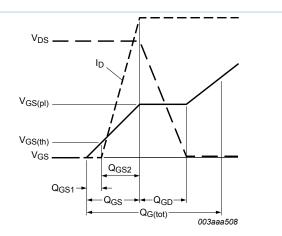


Fig. 15. MOSFET transistor: Gate charge waveform definitions

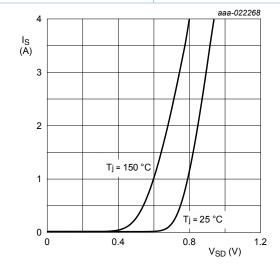
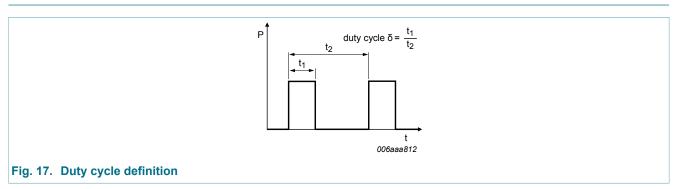


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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# 12. Package outline

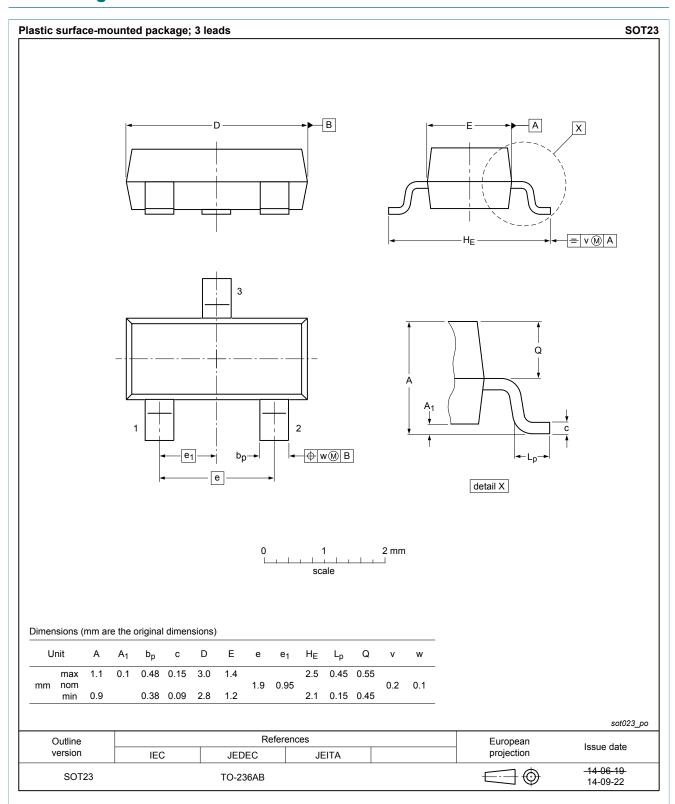


Fig. 18. Package outline TO-236AB (SOT23)

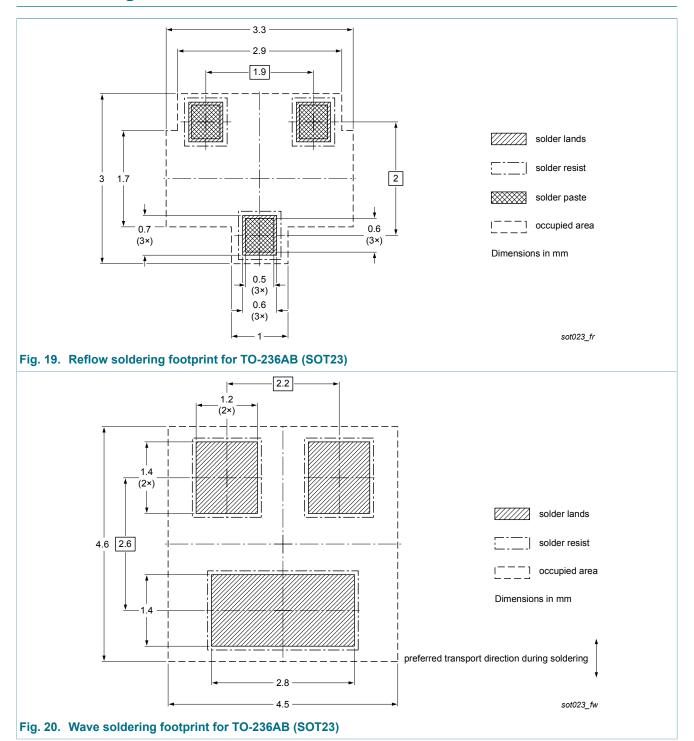
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30 V, N-channel Trench MOSFET

## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV90ENE v.1	20160420	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 30 V, N-channel Trench MOSFET

## 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	5
10	Characteristics	7
11	Test information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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